

Silicon NPN Power Transistors

BU932

DESCRIPTION

- With TO-3 package
- DARLINGTON

APPLICATIONS

- Automotive ignition applications
- Inverters circuits for motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

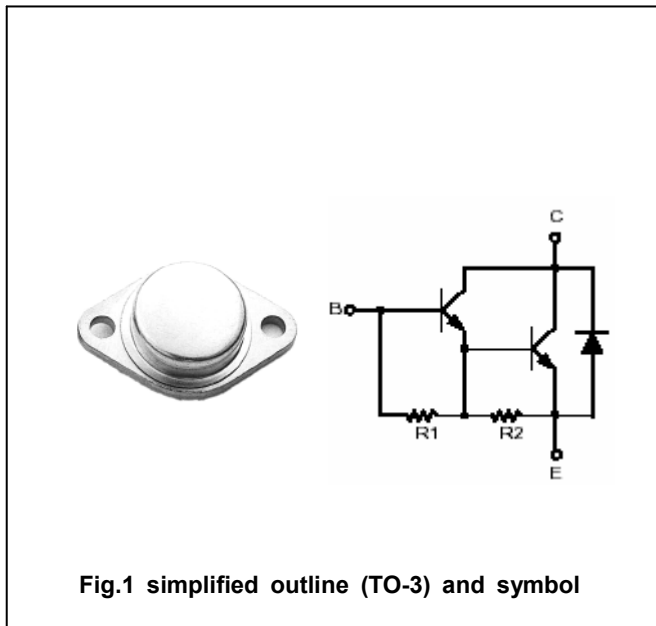


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	450	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		15	A
I <sub>CM</sub>	Collector current-peak		30	A
I <sub>B</sub>	Base current		1	A
I <sub>BM</sub>	Base current-peak		5	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> ≤25°C	150	W
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-40~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.0	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	450			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =150mA			1.8	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =150mA			2.2	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =450V ; I <sub>B</sub> =0			1.0	mA
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =450V ; V <sub>BE</sub> =0 T <sub>C</sub> =125°C			1.0 5.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			50	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =10V	300			
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =10A			2.8	V

PACKAGE OUTLINE



Fig.2 Outline dimensions